Product data sheet COMPANY PUBLIC

1 General description

The BGU8051 is, also known as the BTS1001L, a low noise high linearity amplifier for wireless infrastructure applications, equipped with fast shutdown to support TDD systems. The LNA has a high input and output return loss and is designed to operate between 0.3 GHz and 1.5 GHz. It is housed in a 2 mm \times 2 mm \times 0.75 mm 8-terminal plastic thin small outline package. The LNA is ESD protected on all terminals.

2 Features and benefits

- Low noise performance: NF = 0.43 dB
- High linearity performance: IP3_O = 39 dBm
- High input return loss > 15 dB
- High output return loss > 20 dB
- · Unconditionally stable
- Programmable bias current (via resistor)
- Small 8-terminal leadless package 2 mm × 2 mm × 0.75 mm
- · ESD protection on all terminals
- · Moisture sensitivity level 1
- Fast shut down to support TDD systems
- 3 V to 5 V single supply

3 Applications

- · Wireless infrastructure
- · Low noise and high linearity applications
- LTE, W-CDMA, CDMA, GSM
- · General-purpose wireless applications
- TDD or FDD systems
- · Suitable for small cells



Low noise high linearity amplifier

4 Quick reference data

Table 1. Quick reference data

f = 900 MHz, V_{CC} = 5 V, T_{amb} = 25 °C, input and output 50 Ω ; R_{bias} = 5.1 k Ω ; unless otherwise specified. All RF parameters are measured in an application board as shown in Figure 16 with components listed in Table 9 optimized for f = 900 MHz.

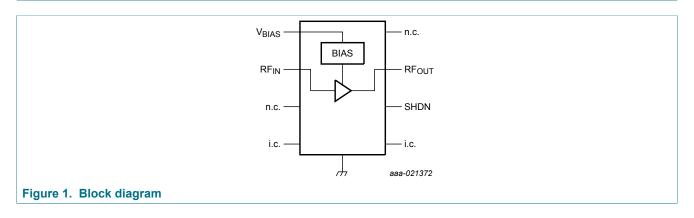
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CC}	supply current	on state	36	48	60	mA
		off state	-	2.8	-	mA
G _{ass}	associated gain	on state	17	18.3	20	dB
		off state	-	-21	-	dB
NF	noise figure		-	0.43	0.63	dB
P _{L(1dB)}	output power at 1 dB gain compression		-	19	-	dBm
IP3 _O	output third-order intercept point	2-tone; tone spacing = 1 MHz;P _i = -15 dBm per tone	35	39	-	dBm

5 Ordering information

Table 2. Ordering information

Type number	Package	ackage							
	Name	Description	Version						
BGU8051	HWSON8	plastic thermal enhanced very very thin small outline package; no leads; 8 terminals; body 2 × 2 × 0.75 mm	SOT1327-1						

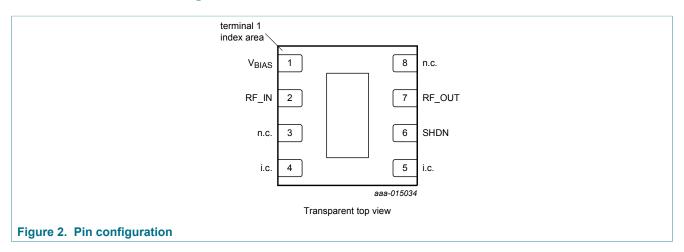
6 Block diagram



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7 Pinning information

7.1 Pinning



7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
V _{BIAS}	1	bias voltage
RF_IN	2	RF input
n.c.	3, 8	not connected
i.c.	4, 5	internally connected. Can be grounded or left open in the application
SHDN	6	shutdown
RF_OUT	7	RF output
GND	exposed die pad	ground

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Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-	6	V
V _{ctrl(sd)}	shutdown control voltage			-	3	V
I _{CC}	supply current			-	85	mA
P _{i(RF)CW}	continuous waveform RF input power			-	20	dBm
T _{stg}	storage temperature			-40	+150	°C
T _j	junction temperature			-	150	°C
Р	power dissipation	T _{case} ≤ 125 °C	[1]	-	510	mW
V_{ESD}	electrostatic discharge voltage	Human Body Model (HBM) According to ANSI/ESDA/JEDEC standard JS-001-2010		-	1.5	kV
		Charged Device Model (CDM); According to JEDEC standard 22-C101B		-	2	kV

Case is ground solder pad.

Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		3.3	5	5.25	V
Z_0	characteristic impedance		-	50	-	Ω
T _{case}	case temperature		-40	-	+85	°C

10 Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{\text{th(j-case)}}$	thermal resistance from junction to case	[1] [2]	50	K/W

Case is ground solder pad.

Thermal resistance measured using infrared measurement technique, device mounted on application board and placed in still air.

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11 Characteristics

Table 7. Characteristics

f = 900 MHz, V_{CC} = 5 V, T_{amb} = 25 °C, input and output 50 Ω ; R_{bias} = 5.1 k Ω ; unless otherwise specified. All RF parameters are measured in an application board as shown in Figure 16 with components listed in Table 9 optimized for f = 900 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CC}	supply current	on state	36	48	60	mA
		off state	-	2.8	-	mA
G _{ass}	associated gain	on state	17	18.3	20	dB
		off state	-	-21	-	dB
NF	noise figure		-	0.43	0.63	dB
P _{L(1dB)}	output power at 1 dB gain compression		-	19	-	dBm
IP3 _O	output third-order intercept point	2-tone; tone spacing = 1 MHz;P _i = -15 dBm per tone	35	39	-	dBm
		2-tone; tone spacing = 1 MHz;P _i = -15 dBm per tone	33	37	-	dBm
RLin	input return loss	on state	-	15.9	-	dB
		off state	-	12.5	-	dB
RLout	output return loss		-	29	-	dB
ISL	isolation		-	21	-	dB
t _{s(pon)}	power-on settling time	P _i = -20 dBm; SHDN (pin 6) from HIGH to LOW [1]	-	1.4	-	μs
t _{s(poff)}	power-off settling time	P _i = -20 dBm; SHDN (pin 6) from LOW to HIGH [1]	-	0.4	-	μs
K	Rollett stability factor	both on state and off state up to f = 20 GHz	1	-	-	
R _{pd(SHDN)}	pull-down resistance on pin SHDN		-	10	-	kΩ

^[1] For applications where fast switching is required, the value of C1 and C2 should be changed to 100 pF.

Table 8. Shutdown control

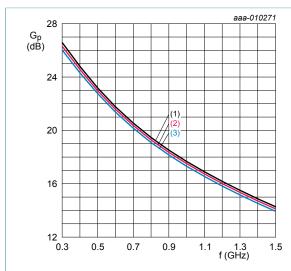
 V_{CC} = 5 V, T_{amb} = 25 °C, input and output 50 Ω ; R_{bias} = 5.1 k Ω ; unless otherwise specified. All RF parameters are measured in an application board as shown in Figure 16 with components listed in Table 9 optimized for f = 900 MHz.

State	V _{ctrl(sd)} ^[1]	Unit
on state	≤ 0.6	V
off state	≥ 1.2	V

[1] Voltage on pin 6 (SHDN).

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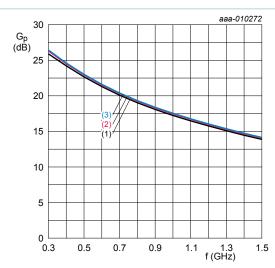
11.1 Graphics



V_{CC}= 5 V; I_{CC}= 48 mA.

- (1) T_{amb} =-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +85^{\circ}C$

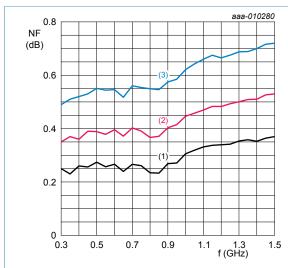
Figure 3. Power gain as a function of frequency; typical values



V_{CC}= 5 V; T_{amb}= 25°C.

- (1) I_{CC} = 30 mA
- (2) I_{CC} = 45 mA
- (3) I_{CC} = 60 mA

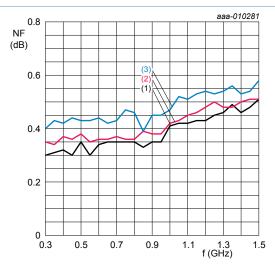
Figure 4. Power gain as a function of frequency; typical values



 V_{CC} = 5 V; I_{CC} = 48 mA.

- (1) T_{amb} =-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +85^{\circ}C$

Figure 5. Noise figure as a function of frequency; typical Figure 6. Noise figure as a function of frequency; typical



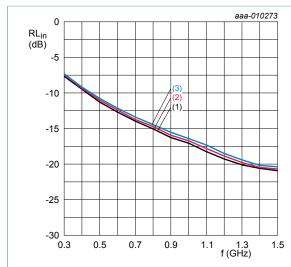
 V_{CC} = 5 V; T_{amb} = 25°C.

- (1) I_{CC} = 30 mA
- (2) I_{CC} = 45 mA
- (3) I_{CC} = 60 mA

values

BGU8051

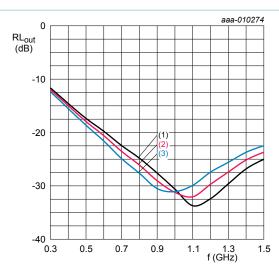
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 V_{CC} = 5 V; I_{CC} = 48 mA.

- (1) T_{amb}=-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +85^{\circ}C$

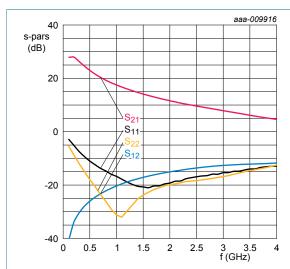
Figure 7. Input return loss as a function of frequency; typical values



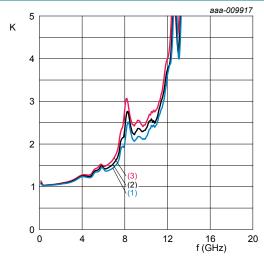
 V_{CC} = 5 V; I_{CC} = 48 mA.

- (1) T_{amb}=-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +85^{\circ}C$

Figure 8. Output return loss as a function of frequency; typical values



 V_{CC} = 5 V; T_{amb} = 25°C; I_{CC} = 48 mA.



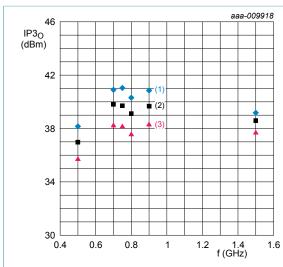
 V_{CC} = 5 V; I_{CC} = 48 mA.

- (1) $T_{amb} = -40^{\circ}C$
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +85^{\circ}C$

Figure 10. Rollett stability factor as a function of frequency; typical values

Figure 9. Wideband S-parameters as function of frequency; typical values

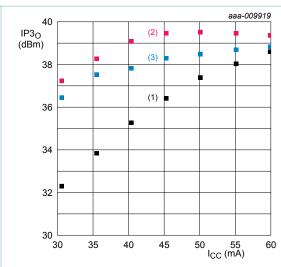
Low noise high linearity amplifier



 V_{CC} = 5 V; P_i =-15 dBm per tone; I_{CC} = 48 mA.

- (1) T_{amb}=-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +85^{\circ}C$

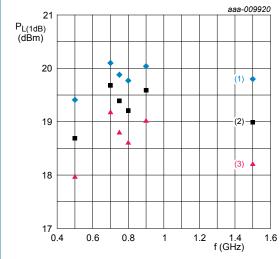
Figure 11. Output third-order intercept point as a function of frequency; typical values



 V_{CC} = 5 V; P_i =-15 dBm per tone; T_{amb} = 25°C.

- (1) f = 500 MHz
- (2) f = 900 MHz
- (3) f = 1500 MHz

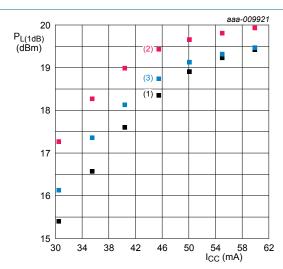
Figure 12. Output third-order intercept point as a function of supply current; typical values



 V_{CC} = 5 V; I_{CC} = 48 mA.

- (1) T_{amb}=-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +85^{\circ}C$

Figure 13. Output power at 1 dB gain compression as a function of frequency; typical values

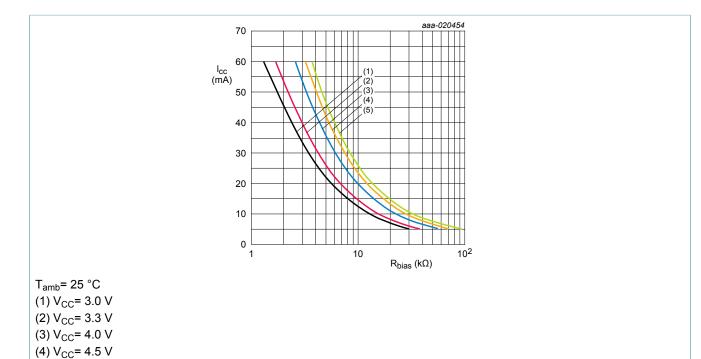


 V_{CC} = 5 V; T_{amb} = 25°C.

- (1) f = 500 MHz
- (2) f = 900 MHz
- (3) f = 1500 MHz

Figure 14. Output power at 1 dB gain compression as a function of supply current; typical values

Low noise high linearity amplifier



(5) V_{CC}= 5 V

Figure 15. I_{CC}as a function of R_{bias}; typical values

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12 Application information

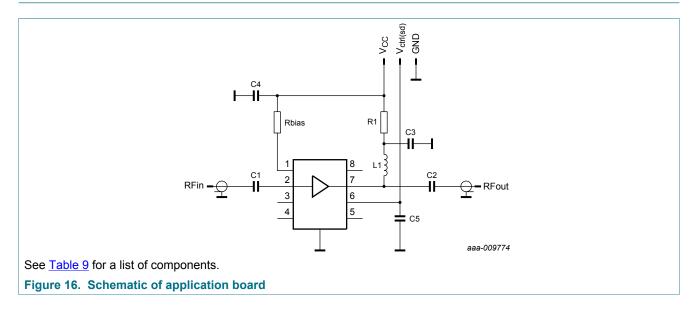


Table 9. List of components

See Figure 16 for schematics.

Component	Description	Value	Remarks
C1, C2	capacitor	100 nF	
		100 pF	recommended for TDD systems
C3, C5	capacitor	10 pF	
C4	capacitor	10 nF	
L1	inductor	33 nH	
R1	resistor	10 Ω	
R _{bias}	resistor	5.1 kΩ	V _{CC} = 5 V
		2.3 kΩ	V _{CC} = 3.3 V

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Table 10. Typical performance BGU8051 application board V_{CC} = 5 V

All RF parameters are measured at the application board as shown in Figure 16 with the components as listed in Table 9 while optimized for: f = 900 MHz, $V_{CC} = 5 \text{ V}$, $I_{CC} = 48 \text{ mA}$ and $T_{amb} = 25 ^{\circ}\text{C}$. Unless otherwise specified.

Symbol	Parameter	Conditions	f (MHz)							
			400	500	700	750	800	900	1500	
G	gain		24.6	23.0	20.4	19.8	19.3	18.3	14.1	
RLin	input return loss		9.3	11.0	13.7	14.2	14.7	15.9	20.7	
RL _{out}	output return loss		15.0	18.0	23.5	24.8	26.1	29.0	23.7	
P _{L(1dB)}	output power at 1 dB gain compression		17.9	18.8	19.8	18.7	19.4	19.4	18.5	
IP3 _O	output third-order intercept point	[1]	35.5	37.9	39.5	39.6	39.8	39.9	39.2	
		[1]	35.6	37.2	38.8	39.3	39.1	39.8	38.2	
NF	noise figure	[3]	0.41	0.39	0.40	0.39	0.37	0.40	0.43	

^[1] For 2 Tone: tone spacing = 1MHZ, Po=5 dBm per tone

Table 11. Typical performance BGU8051 application board V_{CC} = 3.3 V

All RF parameters measured at application board shown in Figure 16. The components listed in Table 9 optimized for 1900 MHz; V_{CC} = 3.3 V; I_{CC} = 48 mA; T_{amb} = 25 °C.

Symbol	Parameter	Conditions	f (MHz)						
			400	500	700	750	800	900	1500
G	gain		24.5	22.9	20.4	19.8	19.3	18.2	14.0
RLin	input return loss		9.1	10.5	14.1	13.5	14.1	14.3	19.2
RLout	output return loss		16.8	18.1	22.3	22.4	24.1	25.0	26.5
P _{L(1dB)}	output power at 1 dB gain compression		15.9	16.4	16.6	16.1	16.3	16.3	15.4
IP3 _O	output third-order intercept point	[1]	32.4	34.3	35.5	34.5	34.1	35.3	31.6
		[1]	32.4	33.1	33.6	33.6	33.1	33.2	30.2
NF	noise figure	[3]	0.39	0.40	0.42	0.43	0.44	0.44	0.43

^[1] For 2 Tone: tone spacing = 1MHZ, Po=5 dBm per tone

^[2] For applications where fast switching is required, the value of C1 and C2 should be changed to 100 pF.

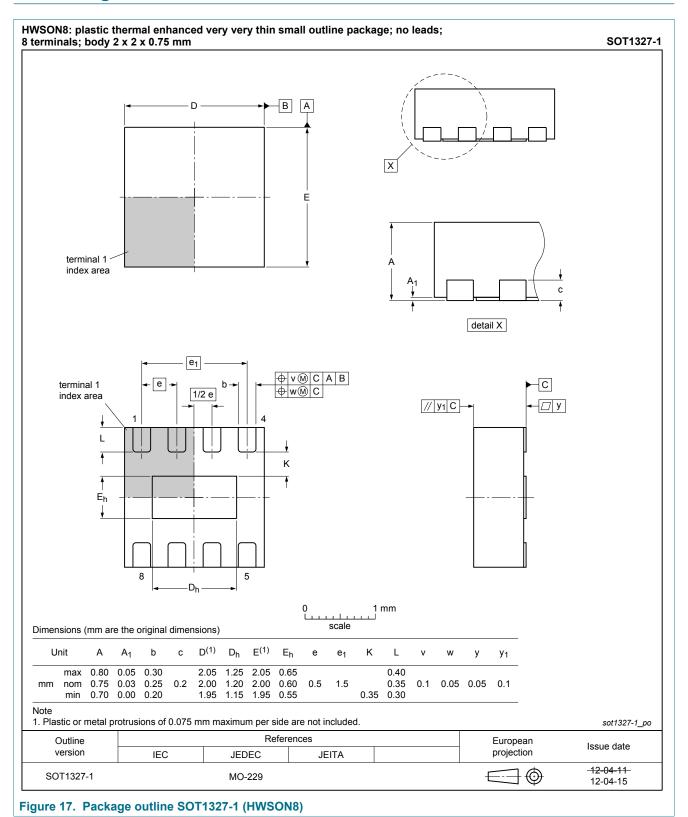
^{3]} Connector and board losses not de-embedded.

^[2] For applications where fast switching is required, the value of C1 and C2 should be changed to 100 pF.

^[3] Connector and board losses not de-embedded.

Low noise high linearity amplifier

13 Package outline



Low noise high linearity amplifier

14 Abbreviations

Table 12. Abbreviations

Acronym	Description
CDMA	Code Division Multiple Access
ESD	ElectroStatic Discharge
FDD	Frequency-Division Duplexing
GSM	Global System for Mobile Communication
LNA	Low Noise Amplifier
LTE	Long-Term Evolution
RF	Radio Frequency
TDD	Time-Division Duplexing
W-CDMA	Wideband Code Division Multiple Access

15 Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BGU8051 v.7	20170608	Product data sheet	-	BGU8051 v.6		
Modifications:	<u>Table 4</u> : the maximum value of V _{ESD} has been changed into 1.5 kV					
BGU8051 v.6	20170502	Product data sheet	-	BGU8051 v.5		
Modifications:	<u>Table 5 "Recommended operating conditions"</u> : the minimum value of V _{CC} has been changed into 3.3 V					
BGU8051 v.5	20170120	Product data sheet	-	BGU8051 v.4		
Modifications:	<u>Section 1 "General description"</u> : added BTS1001L according to our new naming convention					
BGU8051 v.4	20160418	Product data sheet	-	BGU8051 v.3		
Modifications:	 3 V to 5 V single supply, added to <u>Section 2 "Features and benefits"</u> An additional curve added to <u>Figure "Output power at 1 dB gain compression as a function of supply current; typical values" on page 8</u> Added <u>Table 11 "Typical performance BGU8051 application board VCC = 3.3 V" on page 11</u> Added <u>Figure 1 "Block diagram" on page 2</u> Added remark to R_{bias} in <u>Table 9 "List of components"</u> 					
BGU8051 v.3	20140929	Product data sheet	-	BGU8051 v.2		
Modifications:	Figure 1 on page 2: figure has been corrected					
BGU8051 v.2	20131230	Product data sheet	-	BGU8051 v.1		
BGU8051 v.1	20131127	Product data sheet	-	-		

Low noise high linearity amplifier

16 Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- The term 'short data sheet' is explained in section "Definitions". [2] [3]
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Low noise high linearity amplifier

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BGU8051

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